Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	275	(misfet or mosfet) and (memory or dram or sdram or rom or prom or eeprom or eprom) and (peripheral) near2 (logic or circuit) and (implant or implanting or implanted or implantation) near4 (multiple or multi or multistep or several or ldd or second or third)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/12 11:34
L3	137	(misfet or mosfet) and (memory or dram or sdram or rom or prom or eeprom or eprom) and (peripheral) near2 (logic or circuit) and (implant or implanting or implanted or implantation) near4 (multiple or multi or multistep or several or ldd or two near step or three near step or (side or sidewall or spacer or edge or wall) near2 (mask or masking or masked))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/12 11:35
L4	162	(misfet or mosfet) and (memory or dram or sdram or rom or prom or eeprom or eprom) and (peripheral) near2 (logic or circuit) and (implant or implanting or implanted or implantation) near4 (multiple or multi or multistep or several or ldd or plural or plurality or two near step or three near step or (side or sidewall or spacer or edge or wall) near2 (mask or masking or masked))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/12 11:36
L5	4	("5930618" | "5966600" | "6117723" | "6159839" | "B1 6177306").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/12 11:47
L6	2	("6251721").URPN.	USPAT	OR	ON	2004/11/12 12:08
L7	109	(mosfet or misfet) and (memory) and peripheral and gate near3 (doped or doping or implanted or implanting or dopant) near3 (n or p or "n+" or "p+" or "(n)" or "(p)")	USPAT	OR	ON	2004/11/12 12:22
L8	350	dram and (nmisfet or n near misfet or n-misfet or nmis or nmosfet or nmos or n-mos) near10 (gate) near4 (p or boron or b)	USPAT	OR	ON	2004/11/12 12:23
L9	260	dram and (nmisfet or n near misfet or n-misfet or nmis or nmosfet or nmos or n-mos) near10 (gate) near2 (p or boron or b)	USPAT	OR	ON	2004/11/12 12:25

L10	27	dram and (nmisfet or n near misfet or n-misfet or nmis or nmosfet or nmos or n-mos) near10 (gate) near (doped or doping or dopant or implanted or implanting or implant) near2 (p or boron or b)	USPAT	OR	ON	2004/11/12 12:35
L11	3	("6319779").URPN.	USPAT	OR	ON	2004/11/12 12:32
L12	37	("3660735" | "4149904" | "4198250" | "4356623" | "4697333" | "4703551" | "4745086" | "4760033" | "4859618" | "4935379" | "4949136" | "5147811" | "5185280" | "5217910" | "5227321" | "5244823" | "5272367" | "5296401" | "5321283" | "5395773" | "5401994" | "5405791" | "5424567" | "5439834" | "5482878" | "5489546" | "5500379" | "5534449" | "5536959" | "5595919" | "5614432" | "5650343" | "5654212" | "5719425" | "5747852" | "5866460" | "6004843").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/12 12:32
L13	4	dram and (nmisfet or n near misfet or n-misfet or nmis or nmosfet or nmos or n-mos) and (gate) near (doped or doping or dopant or implanted or implanting or implant) near5 (work near function)	USPAT	OR	ON	2004/11/12 12:37
L14	53	dram and capacitor and (nmisfet or n near misfet or n-misfet or nmis or nmosfet or nmos or n-mos) and (gate) near5 (work near function)	USPAT	OR	ON	2004/11/12 12:54
L16	21	(dram or sdram) and capacitor and (gate) near5 (work near function) near3 (increase or increased or greater or higher or larger or large)	USPAT	OR	ON	2004/11/12 13:04
L17	167	(dram or sdram or memory) and capacitor and (gate) near5 (work near function)	USPAT	OR	ON	2004/11/12 13:30
L18	14	(dram or sdram or memory near8 capacitor) and gate near6 (liner or spacer or sidewall or lining or conformal or wall) near8 hydrogen	USPAT	OR	ON	2004/11/12 13:38
L19	2	(dram or sdram or memory near8 capacitor) and gate near6 (liner or spacer or sidewall or lining or conformal or wall or cover or covering) near12 barrier near4 (hydrogen or h)	USPAT	OR	ON	2004/11/12 13:40

L20	10	(dram or sdram or memory near8 capacitor) and (gate near6 (liner or spacer or sidewall or lining or conformal or wall or cover or covering) or gate near2 (dielectric or insulator or oxide)) near12 (little or "no" or minimum or minimal or barrier) near2 (hydrogen or h)	USPAT	OR	ON	2004/11/12 13:42
L21	5	(transistor or fet or mosfet or nmos or pmos or misfet or nmis or pmis) and (gate near6 (liner or spacer or sidewall or lining or conformal or wall or cover or covering) or gate near2 (dielectric or insulator or oxide)) near6 (little or "no" or minimum or minimal or free) near2 (hydrogen or h)	USPAT	OR	ON	2004/11/12 13:58
L22	3937	(transistor or fet or mosfet or nmos or pmos or misfet or nmis or pmis) and (gate near6 (liner or spacer or sidewall or lining or conformal or wall or cover or covering)) near6 (polysilicon or polycrystalline near silicon or poly near si or poly near silicon)	USPAT	OR	ON	2004/11/12 14:00
L23	2563	(transistor or fet or mosfet or nmos or pmos or misfet or nmis or pmis) and (gate near6 (liner or spacer or sidewall or lining or conformal or wall or cover or covering)) near (polysilicon or polycrystalline near silicon or poly near si or poly near silicon)	USPAT	OR	ON	2004/11/12 14:00
L24	1500	(transistor or fet or mosfet or nmos or pmos or misfet or nmis or pmis) and (gate near4 (liner or spacer or sidewall or lining or conformal)) near (polysilicon or polycrystalline near silicon or poly near si or poly near silicon)	USPAT	OR	ON	2004/11/12 14:03
L25	324	(dram or sdram or memory near10 capacitor) and (gate near4 (liner or spacer or sidewall or lining or conformal)) near (polysilicon or polycrystalline near silicon or poly near si or poly near silicon)	USPAT	OR	ON	2004/11/12 14:02
L26	300	(transistor or fet or mosfet or nmos or pmos or misfet or nmis or pmis) and (gate near6 (polysilicon or polycrystalline near silicon or poly near si or poly near silicon) adj (liner or spacer or sidewall or lining or conformal))	USPAT	OR	ON	2004/11/12 14:12

L27	37	(dram or sdram) and (gate near6 (polysilicon or polycrystalline near silicon or poly near si or poly near silicon) adj (liner or spacer or sidewall or lining or conformal))	USPAT	OR	ON	2004/11/12 14:15
L28	873	(dram or sdram) and capacitor and (peripheral) near (circuit or transistor or mosfet or misfet or nmos or pmos or nmis or pmis or hvfet or area or logic or region) and (source or drain or impurity or ldd) near3 (implant or implanting or implanted or implantation)	USPAT	OR	ON	2004/11/12 14:17
L29	568	(dram or sdram) and capacitor and (peripheral) near (circuit or transistor or mosfet or misfet or nmos or pmos or nmis or pmis or hvfet or area or logic or region) and (source or drain or impurity or ldd) near3 (implant or implanting or implanted or implantation) and gate near5 (spacer or sidewall or wall or cover or side near wall)	USPAT	OR	ON	2004/11/12 14:40
L30	215	(dram or sdram) and capacitor and (peripheral) near (circuit or transistor or mosfet or misfet or nmos or pmos or nmis or pmis or hvfet or area or logic or region) and (source or drain or impurity or ldd) near3 (implant or implanting or implanted or implantation) and gate near5 (spacer or sidewall or wall or cover or side near wall) near10 (mask or masking or masked or implant or implanting or implantation or implanted)	USPAT	OR	ON	2004/11/12 15:00
L31	1	"6153490".pn.	USPAT	OR	ON	2004/11/12 15:00
S1	214	misfet and memory and peripheral and capacitor not hitachi.asn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:35
S2	390	misfet and memory and peripheral and capacitor not S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:52
S3	1041	misfet and memory and peripheral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/10 16:21

S4	603	misfet and memory and peripheral and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:50
S5	58	(misfet or mosfet) and (memory or dram or sdram or rom or prom or eeprom or eprom) and (peripheral) near2 (logic or circuit) and (sidewall or side near wall or spacer or wall) near4 (mask or masking or protection or blocking or blocker or protecting) near4 (implant or implanting or implantation or implanted)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/12 11:33
S6	14	(US-20010022369-$ or US-20010024859-$ or US-20020043680-$ or US-20020047150-$ or US-20020084477-$ or US-20030041803-$ or US-20030183941-$ or US-20040043546-$ or US-20040121526-$ or US-20040147077-$ or US-20040195611-$).did. or (US-6777279-$ or US-6800888-$ or US-6465335-$).did.	US-PGPUB; USPAT	OR	ON	2004/11/10 16:41